

## Table of Contents

### Preface

<b>Trends and Challenges for Advanced Silicon Technologies</b> C. Claeys and L. Deferm	1
<b>Needs of Low Thermal Budget Processing in SiGe Technology</b> U. König and J. Hersener	17
<b>History and Future of Semiconductor Wafer Bonding</b> U.M. Gösele, H. Stenzel, M. Reiche, T. Martini, H. Steinkirchner and Q.-. Tong	33
<b>Building the Electron Superhighway: Back-End Processing and Simulation</b> F.H. Baumann	45
<b>Role of Interstitial Atoms in Microscopic Processes on (113) and (001) Surfaces of Silicon</b> J. Dąbrowski, H.J. Müssig and G. Wolff	57
<b>Silicon Materials and Metrology: Critical Concepts for Optimal IC Performance in the Gigabit Era</b> H.R. Huff and R.K. Goodall	65
<b>Expected Limits for Manufacturing Very Large Silicon Wafers</b> W. v. Ammon	97
<b>Diameter Effects on Grown-In Defects in CZ Crystal Growth</b> F. Uberti and K. Hagimoto	107
<b>Silicon Carbide - A Promising Wide-Band-Gap Semiconductor for Electronic Devices</b> G. Pensl and T. Troffer	115
<b>Multicrystalline Silicon for Solar Cells</b> H.J. Möller	127
<b>Room Temperature UHV Silicon Direct Bonding</b> F. Shi, G. Elssner, M. Reiche and U.M. Gösele	143
<b>External Gettering for Multicrystalline Silicon Wafers</b> S. Martinuzzi and I. Périchaud	153
<b>Gettering of Transition Metals in Multicrystalline Silicon for Photovoltaic Applications</b> E.R. Weber, S.A. McHugo and H. Hieslmair	165
<b>Gettering of Au in Heat Treated Si/SiGe/Si Structures</b> K. Schmalz, D. Krüger, R. Kurps, T. Morgenstern and H.P. Zeindl	171
<b>Gettering of Low Concentration Copper, Nickel and Iron Contamination in Czochralski Silicon Wafers</b> Z. Laczik, L. Bouwhuis, G.R. Booker and R.J. Falster	177
<b>Defect Engineering for Silicon-on-Insulator, MeV Implantation and Low Temperature Processing</b> S.V. Koveshnikov, A.K. Agarwal, K.L. Beaman and G.A. Rozgonyi	183
<b>Interactions between Dopants and End-of-Range Defects in Silicon</b> A. Claverie, C. Bonafos, A. Martinez and D. Alquier	195
<b>Behaviour of the Size Distribution Function of End-of-Range Dislocation Loops during Silicon Oxidation</b> M. Seibt and E. Spiecker	205
<b>SiC Buried Layer Formation Induced by Ion Implantation</b> N.I. Klyui, D. Krüger, B.N. Romanyuk, V.G. Litovchenko and H. Richter	211
<b>The Mechanisms and Application of Dislocation Related Radiation for Silicon Based Light Sources</b> E.A. Steinman, V.V. Kveder and H.G. Grimmeiss	217
<b>Critical Conditions for the Generation of the Misfit Dislocations during the Boron Diffusion in Silicon: Analytical Evaluation</b> F. Gaiseanu	223
<b>Infrared Studies of Oxygen Precipitation Related Defects in Silicon after Various Thermal Treatments</b> J. Vanhellefont, G. Kissinger, P. Clauws, A. Kaniava, M. Libezny, E. Gaubas, E. Simoen, H. Richter and C. Claeys	229

<b>Point Defects in Semiconductors - Then and Now</b> S.T. Pantelides	237
<b>Oxygen Aggregation Phenomena in Silicon</b> R.C. Newman, M.J. Binns, C.A. Londos, S.A. McQuaid and J.H. Tucker	247
<b>New Donors in Heat-Treated Cz-Si, Their Components and Formation Kinetics</b> V.V. Emtsev, G.A. Oganesyanyan and K. Schmalz	259
<b>Hydrogen Passivation of Double Donors in Silicon</b> Y.V. Martynov, I.S. Zevenbergen, T. Gregorkiewicz and C.A.J. Ammerlaan	267
<b>Phosphorus Diffusion Induced Reconstruction of Defect Structure in Oxygen Precipitated Si</b> E.B. Yakimov, I. Périchaud and S. Martinuzzi	275
<b>New Infrared Bands in Neutron-Irradiated Si</b> C.A. Londos, G.I. Georgiou, L.G. Fytros and N. Sarlis	281
<b>Iron Group Impurities in Semiconducting Iron Disilicide</b> K. Irmscher, W. Gelhoff, Y. Tomm and H. Lange	287
<b>Fermi-Level Shifts Caused by Reactions of Intrinsic Defects at 450°C - 540°C in FZ- and Cz-Silicon Supersaturated with Platinum- An Electron Paramagnetic Resonance Study</b> J. Juda and M. Höhne	293
<b>Influence of Point Defects on Defect Formation in Si:Er</b> N.A. Sobolev, O.V. Alexandrov, V.V. Emtsev, M.I. Makovijchuk, A.V. Merkulov, E.O. Parshin, D.S. Poloskin and E.I. Shek	299
<b>The Si:Er Crystal: Model and Excitation Mechanism of the Er-O Center</b> N.T. Bagraev, D.E. Onopko and A.I. Ryskin	307
<b>Point Defect Concentrations, Distributions and Diffusivity in Thin Si MBE-Films: Experiments and Simulations Based on Profiling of Implanted Multiple Delta Doping Structures</b> D. Krüger, R. Kurps, H.P. Zeindl and U. Jagdhold	313
<b>DX-Like Centers in Dislocated Compound Semiconductors: A New Aspect of the Interaction between Extended Defects and Impurities</b> A.A. Istratov and O.F. Vyvenko	319
<b>DRAM Wafer Qualification Issues: Oxide Integrity vs. D-Defects, Oxygen Precipitates and High Temperature Annealing</b> J.G. Park and G.A. Rozgonyi	327
<b>Copper Precipitation in Monocrystalline Silicon: Role of Initial Oxygen Concentration and Thermal Oxidation</b> A. Correia, A. Boutry-Forveille and D. Ballutaud	353
<b>Structural and Electrical Properties of NiSi<sub>2</sub> Particles in Silicon</b> F. Riedel, J. Kronewitz, U. Gnauert, M. Seibt and W. Schröter	359
<b>Contrastive Recombination Behaviour of Metal Silicide and Oxygen Precipitates in n-Type Silicon: Attempt at an Explanation</b> W. Seifert, M. Kittler, M. Seibt and A. Buczkowski	365
<b>Characterisation of High-Energy Proton Irradiation Induced Recombination Centers in Silicon</b> A. Kaniava, J. Vanhellefont, E. Simoen, C. Claeys and E. Gaubas	371
<b>A Study of Defects Generated by BF<sub>2</sub><sup>+</sup> Implantation in Silicon Crystals and Their Annealing</b> K. Lal, G. Bhagavannarayana and G.S. Viridi	377
<b>Surface Damage Induced by Reactive Ion Etching in n- Type Silicon</b> A. Poggi and E. Susi	383
<b>The Effect of Metallization Induced Defects on Metal-Semiconductor Contacts</b> S.A. Goodman, F.D. Auret, G. Myburg and C. Schutte	391
<b>The Impact of Fe and Cu Contamination in the 10<sup>12</sup> at/cm<sup>2</sup> Range on the Performance of Junction Diodes</b> A.L.P. Rotondaro, E. Vandamme, J. Vanhellefont, E. Simoen, M. Heyns and C. Claeys	397
<b>Low-Frequency Noise Sources Related to Processing-Induced Extended Defects in Si Devices</b> E. Simoen, J. Vanhellefont and C. Claeys	403
<b>Correlation between Dislocations and Electron Transport Properties in Si/SiGe</b> K. Ismail	409

<b>Dislocation Related Electroluminescence at Room Temperature in Plastically Deformed Silicon</b>	
V.V. Kveder, E.A. Steinman and H.G. Grimmeiss	419
<b>Investigation of the Dislocation Motion in the Bulk SiGe Crystals</b>	
Y.L. Iunin, V.I. Nikitenko, V.I. Orlov, N.V. Abrosimov, S.N. Rossolenko and W. Schröder	425
<b>Ion Beam Sputter Deposited Si<sub>0.8</sub>Ge<sub>0.2</sub> Epilayers: Lattice Defects and Surface Topology</b>	
V. Demuth, W. Dorsch, H.P. Strunk, M. Lyakas, M. Eizenberg, N. Mosleh, F. Meyer and C. Schwebel	431
<b>GaAIAs Lattice Parameter Dependence on Free Electron Concentration</b>	
J. Bak-Misiuk, M. Leszczyński, J.Z. Domagała and J. Trela	437
<b>Relation between Structural and Carrier Recombination Properties in As-Rich GaAs</b>	
V. Jasutis, D. Lescinskas, S. Marcinkevičius, K. Bertulis, A. Krotkus, H.H. Tan and C. Jagadish	443
<b>Investigation of Microdefects in Multicrystalline Silicon for Photovoltaic Applications</b>	
M. Werner, E.R. Weber, S.A. McHugo, H. Hieslmair and K.L. Chapman	449
<b>Analysis of <math>\Sigma=3</math> and <math>\Sigma=9</math> Twin Boundaries in Three-Crystal Silicon Ingots</b>	
A. Castaldini, D. Cavalcoli, A. Cavallini, G. Martinelli, D. Palmeri, A. Parisini and G. Sartori	455
<b>Band Structure Engineering in Si-Ge Structures</b>	
M. Jaros	463
<b>Diffusion Effects and Luminescence in Thin SiGe/Si Layers</b>	
M. Gail, W. Jung, J. Brunner, P. Schittenhelm, J.F. Nützel and G. Abstreiter	473
<b>Investigation of the Substrate / Epitaxial Interface of Si/Si<sub>1-x</sub>Ge<sub>x</sub> Grown by LPCVD</b>	
R. Loo, L. Vescan, C. Dieker, D. Freundt, A. Hartmann and A. Mück	485
<b>The Effect of Interface Engineering and Wave Function Localisation on Optical Response in Imperfect Type I and Type II Quantum Well Structures</b>	
M.J. Shaw, P.R. Briddon and M. Jaros	491
<b>Mechanisms of Dislocation Generation in Heterostructures Based on SiGe Alloys</b>	
V.I. Vdovin, M.G. Mil'vidskii and T.G. Yugova	497
<b>Elastic and Plastic Stress Relaxation in Stripes and Circular Mesas</b>	
S.C. Jain, K. Pinaridi, A.H. Harker and H. Richter	503
<b>Composition Dependence of Hardness and Elastic Modulus in Si-Ge Measured by Nanoindentation - Possible Consequences for Elasto-Plastic Relaxation and Diffusion</b>	
B. Roos, H. Richter and J. Wollweber	509
<b>The Relaxation and Diffusion Behaviour of Strained Si<sub>1-x</sub>Ge<sub>x</sub> Layers on Si Substrates at High Temperature under Hydrostatic Pressure</b>	
P. Zaumseil, G.G. Fischer, C. Quick and A. Misiuk	517
<b>Critical Points of Strained Si<sub>1-y</sub>C<sub>y</sub> Layers on Si(001)</b>	
W. Kissinger, M. Weidner, H.J. Osten and M. Eichler	523
<b>Dislocation-Related Photoluminescence in Graded SiGe Buffer Layers Grown by APCVD</b>	
H.B. Erzgräber, G. Kissinger, G. Morgenstern and T. Morgenstern	529
<b>Elastic Relaxation of Pseudomorphic Strain in Quantum Dots</b>	
B. Dietrich, H. Frankenfeldt, Y.S. Tang, C.M. Sotomayor Torres, H.P. Zeindl and A. Wolff	535
<b>Electrical Activity of Misfit Dislocations in GaAsSb/GaAs Heterojunctions</b>	
T. Wosiński, A. Makosa and J. Raczynska	541
<b>Twin Formation during Epitaxial Growth of InP on Si</b>	
H.-. Wehmann, G.-. Tang, A. Koch, M. Seibt and A. Schlachetzki	547
<b>Interface Structure and Dislocation Formation in InGaAs/GaAs SQWs Grown with Different In Content on Vicinal Substrates</b>	
C. Frigeri, A. Di Paola, D.M. Ritchie, F. Longo, A. Brinciotti, M. Riva and F. Vidimari	553
<b>Determination of Interface Structure and Bonding by Z-Contrast STEM</b>	
S.J. Pennycook, N.D. Browning, M.M. McGibbon, A.J. McGibbon, M.F. Chisholm and D.E. Jesson	561
<b>Tomographic Atom Probe: A New Tool for Nanoscale Characterisation</b>	
M. Leisch	573
<b>PHOTO-EDSR in Plastically Deformed p-Si</b>	
H.G. Grimmeiss, P. Omling and A.I. Shalynin	583
<b>Cyclotron Resonance in Heavily Doped Silicon Quantum Wells</b>	
W. Gehlhoff, N.T. Bagraev and L.E. Klyachkin	589

<b>TEM Analysis of Structure Modification Induced by Additional Carbon Incorporation in Silicon and Si<sub>1-x</sub>Ge<sub>x</sub> Layers Grown with Molecular Beam Epitaxy</b> E. Bugiel, S. Ruvimov and H.J. Osten	595
<b>Measurements of Diffusion Length in Si-SiGe Structures</b> O.V. Kononchuk, G.A. Rozgonyi and E.B. Yakimov	601
<b>Determination of Subgap-Absorption in <math>\mu\text{c-Si:H}</math> Films by CPM</b> R. Krankenhagen, M. Schmidt, W. Henrion, I. Sieber, S. Koynov, S. Grebner and R. Schwarz	607
<b>An Analysis of Residual Strain in Dry Etched Semiconductor Nanostructures</b> Y.S. Tang and C.M. Sotomayor Torres	613